

SOT-23 Plastic-Encapsulate MOSFETS

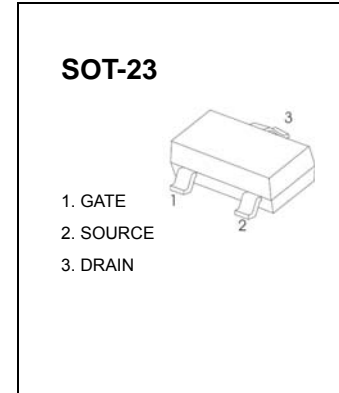
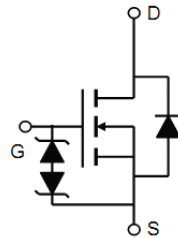
FEATURE

TrenchFET Power MOSFET

APPLICATIONS

- Load Switch for Portable Devices
- DC/DC Converter

MARKING: R34



Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 10	V
Continuous Drain Current	I_D	5	A
Pulsed Drain Current	I_{DM}^*	20	A
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	417	$^{\circ}\text{C}/\text{W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	T_L	260	$^{\circ}\text{C}$

*Repetitive rating: Pluse width limited by junction temperature.

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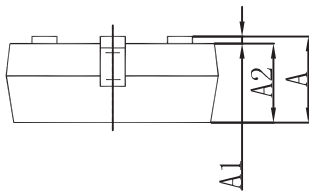
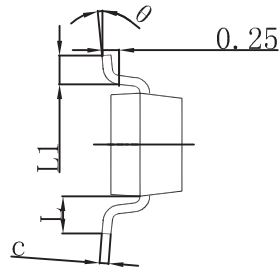
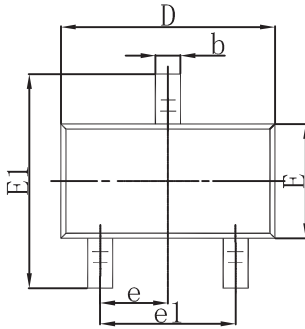
Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
STATIC PARAMETERS						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±10V, V _{DS} = 0V			±10	μA
Gate threshold voltage(note 1)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.6		1	V
Drain-source on-resistance (note 1)	R _{DS(on)}	V _{GS} = 10V, I _D = 5A			42	mΩ
		V _{GS} = 4.5V, I _D = 5A			44	mΩ
		V _{GS} = 2.5V, I _D = 4A			50	mΩ
Forward tranconductance (note 1)	g _{FS}	V _{DS} = 5V, I _D = 4A		15		S
Diode forward voltage (note 1)	V _{SD}	I _S = 1A, V _{GS} = 0V			1	V
DYNAMIC PARAMETERS (note2)						
Input Capacitance	C _{iss}	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz		245		pF
Output Capacitance	C _{oss}			35		pF
Reverse Transfer Capacitance	C _{rss}			20		pF
SWITCHING PARAMETERS (note 2)						
Turn-on delay time	t _{d(on)}	V _{DD} = 15V, V _{GS} = 10V R _L = 3.75Ω, R _{GEN} = 3Ω		2		ns
Turn-on rise time	t _r			3.5		ns
Turn-off delay time	t _{d(off)}			22		ns
Turn-off fall time	t _f			3.5		ns
Total Gate Charge	Q _g	V _{DS} = 15V, V _{GS} = 10V, I _D = 4A			10	nC
Gate-Source Charge	Q _{gs}			0.5		nC
Gate-Drain Charge	Q _{gd}			1		nC

- Notes :**
1. Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 0.5%.
 2. Guaranteed by design, not subject to production testing.

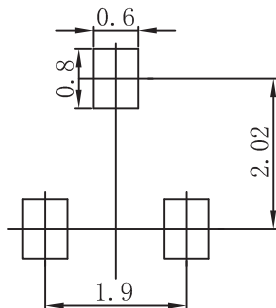
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SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.